

OPA4731

Blue LED Chip

InGaN / Sapphire

1. Material Substrate Sapphire (Insulator)
Epitaxial Layer InGaN

2. Electrode N (Cathode) Side Al Alloy
P (Anode) Side Au Alloy

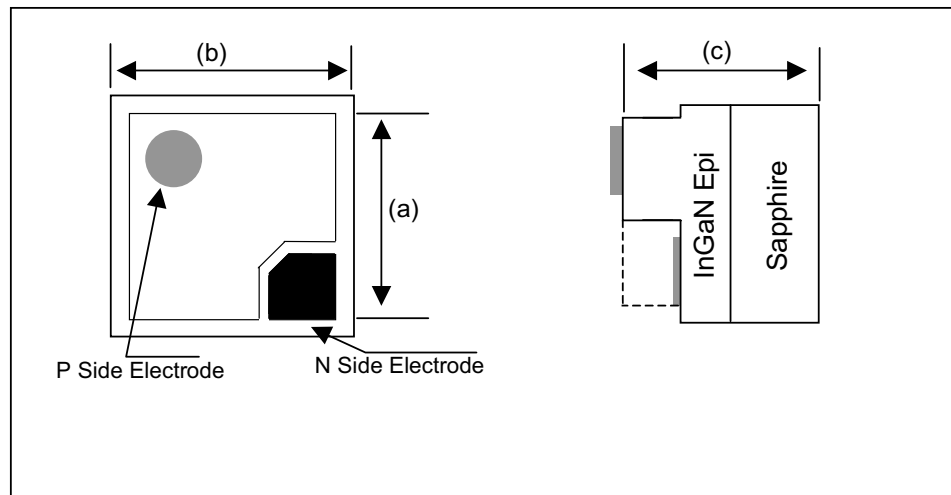
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		3.8		V	$I_F=20\text{mA}$
Reverse Voltage	V_R	5			V	$I_R=10\text{mA}$
Brightness	I_V		500		mcd	$I_F=20\mu\text{A}$
Peak Wavelength	λ_P		465		nm	$I_F=20\text{mA}$
Spectral Bandwidth	$\Delta\lambda$		30		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1^{3/4} plastic package.

4. Mechanical Data

- (a) Emission Area ----- 12mil × 12mil
- (b) Bottom Area ----- 16mil × 16mil
- (c) Chip Thickness ----- 3mil



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